EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	246	"257".clas. and (mosfet or fet) and equivalent with oxide with capacitance	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/10 12:35
S1	2	"US 20060157733"	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2007/09/06 16:34
S2	7	"6097058"	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2007/09/06 16:35
S4	542	"257".clas. and (gadolinium or praseodynium or lutetium) with oxide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/07 17:29
S5	5	("6097058").URPN.	USPAT	OR	OFF	2007/09/06 17:28
S6	1	("6097058").PN.	USPAT; USOCR	OR	OFF	2007/09/07 13:52
S7	7	"257".clas. and ferroelectric and ABO and layer with (nm or nanometer or angstroms) with (thick or thickness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/07 13:56
S8	531	"257".clas. and ferroelectric with layer with (nm or nanometer or angstroms) with (thick or thickness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/07 13:56
S9	86	"257".clas. and ferroelectric with layer with (nm or nanometer or angstroms) with (thick or thickness) with "10"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/07 14:03

S10	130	"257".clas. and ferroelectric with layer with (nm or nanometer or angstroms) with (thick or thickness) and (fet or mosfet)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/07 15:15
S11	0	"257".clas. and (mosfet or fet) and susbstrate with (InGaAsP and InGaAs and (GaAlN or GaInN or AlInN or GaAlInN))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/07 15:17
S12	0	"257".clas. and (mosfet or fet) and susbstrate with (InGaAsP and InGaAs)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/07 15:18
S13	35	"257".clas. and (mosfet or fet) and substrate with (InGaAsP and InGaAs)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/07 16:08
S14	121	"257".clas. and (mosfet or fet) and substrate with (GaAlN or InGaN or InGaAlN or InAlN)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/07 16:32
S15	267	"257".clas. and (mosfet or fet) and gate adj (dielectric or insulat$3) adj layer with (sion or "silicon oxynitride")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/07 16:59
S16	442	"257".clas. and (mosfet or fet) and photovoltaic	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/07 17:18

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S17	667	"257".clas. and (mosfet or fet) with ("high electron mobility" or hemt)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/07 17:26
S18	200	"257".clas. and (mosfet or fet) and "equivalent oxide thickness" with (nm or nanometer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/10 12:33
S19	42	"257".clas. and (gadolinium or praseodynium or lutetium) with oxide and thickness near3 equivalent	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/07 17:30